

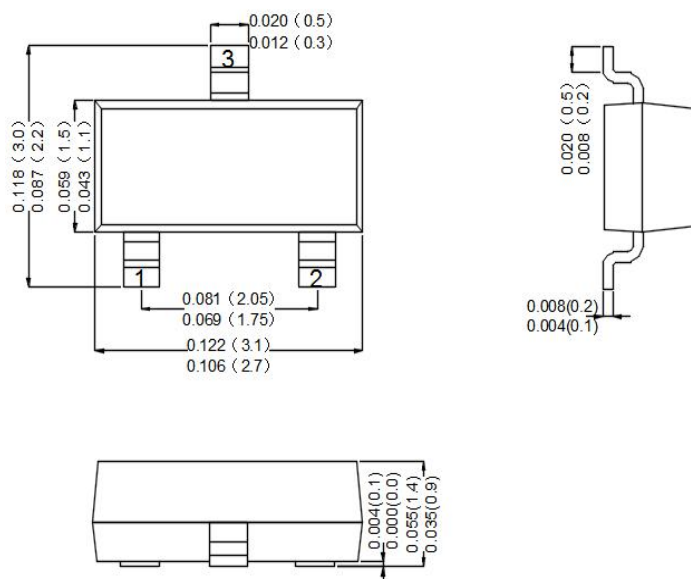


Features

SOT-23

Mechanical Data

- Case: Molded Plastic, SOT-23
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Plated Leads Solderable per MIL-STD-750, Method-2026.
- Marking: marked on body
- Mounting Position : Any.
- Equivalent Circuit:



Dimensions in inches and (millimeters)

Maximum Ratings Maximum Ratings (Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	3	A
Peak Collector Current (t = 10 ms)	$-I_{CP}$	7	A
Base Current	$-I_B$	0.6	A
Total Power Dissipation @ $T_a = 25^\circ\text{C}$	P_D	1	W
Total Power Dissipation @ $T_c = 25^\circ\text{C}$	P_D	10	W
Operating and Storage Junction Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

**Electrical Characteristics** (Rating at 25°C ambient temperature unless otherwise specified.)

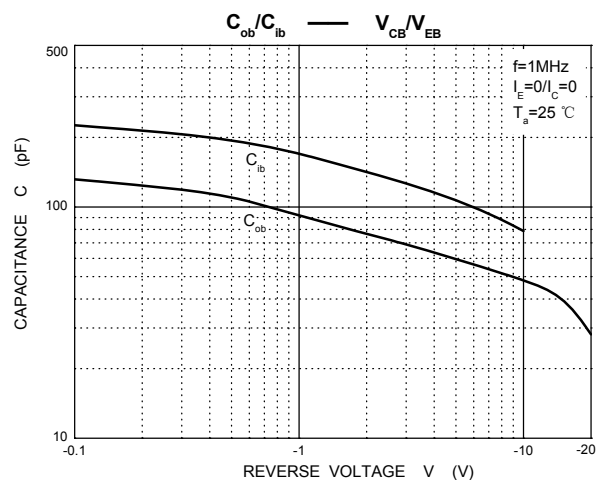
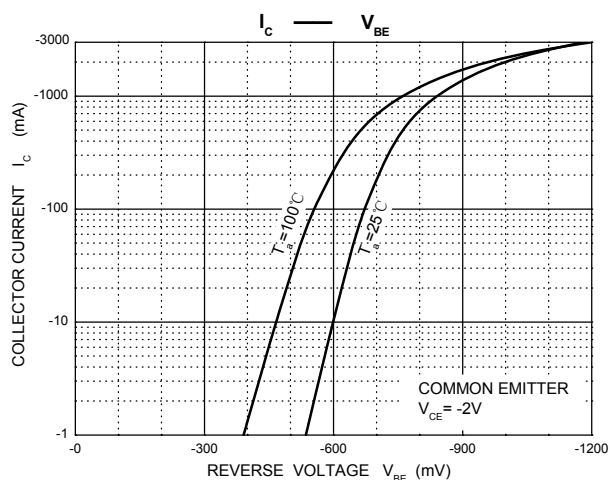
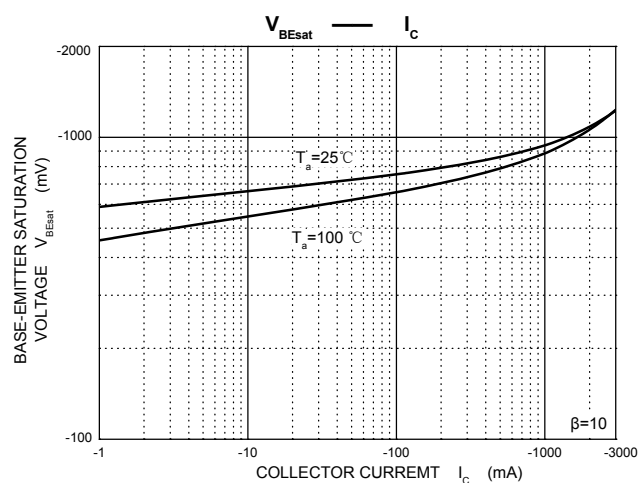
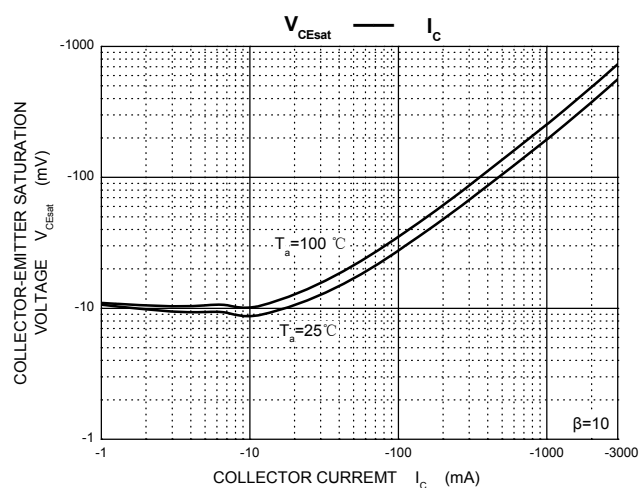
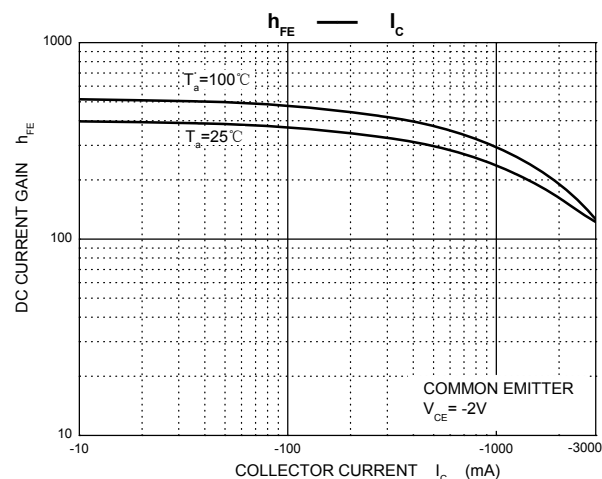
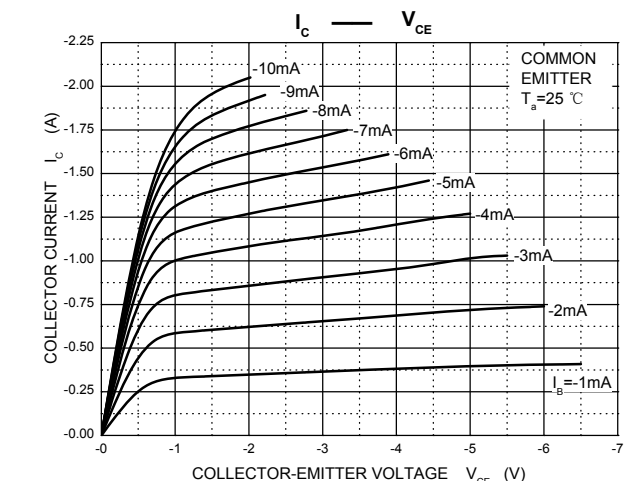
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 20\text{ mA}$ at $-V_{CE} = 2\text{ V}$, $-I_C = 1\text{ A}$ Current Gain Group	h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	30 60 100 160 200	- - - - -	- 120 200 320 400	- - - - -
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	-	1	μA
Emitter Base Cutoff Current at $-V_{EB} = 3\text{ V}$	$-I_{EBO}$	-	-	1	μA
Collector Base Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CBO}$	40	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	30	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 1\text{ mA}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 2\text{ A}$, $-I_B = 200\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V
Base Emitter Saturation Voltage at $-I_C = 2\text{ A}$, $-I_B = 200\text{ mA}$	$-V_{BE(sat)}$	-	-	2	V
Current Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ mA}$,	f_T	-	80	-	MHz
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	55	-	pF



2SB772

PNP SILICON EPITAXIAL POWER TRANSISTOR

Rating And Characteristic Curves





Important Notice and Disclaimer

- Reproducing and modifying information of the document is prohibited without from XINNUO.
- XINNUO reserves the right to make changes to this document and its products and specifications.
- XINNUO disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- XINNUO does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the here in document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. XINNUO makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown her are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify XINNUO for any damages resulting from such improper use or sale.
- Since XINNUO uses lot number as the tracking base, please provide the lot number for tracking when complaining.